



AMERICAN
MICROSEMICONDUCTOR

1N5553 Diodes

General Purpose Fast Rectifier

Military/High-Rel N

$I(O)$ Max.(A) Output Current 3.0

$V(RRM)(V)$ Rep.Pk.Rev. Voltage 800

$t(rr)$ Max.(s) Rev.Rec. Time 2.0u

@ $I(F)$ (A) (Test Condition) 500m

@ $I(R)$ (A) (Test Condition) 1.0

$V(FM)$ Max.(V) Forward Voltage 1.3

@ $I(FM)$ (A) (Test Condition) 9.0

@ $V(RM)$ (V) (Test Condition)

$I(RM)$ Max.(A) Reverse Current 1.0u

@ $V(R)$ (V)(Test Condition) 800

$I(RM)$ Max.(A) Pk. Rev. Current 25u

@ $V(R)$ (V) (Test Condition)

@Temp. (°C) (Test Condition) 100°

Semiconductor Material Silicon

Maximum Operating Temp (°C) 175°

Package Style Axial-B